

## WIDENING OF Si UNDER THE IMPACT OF ILLUMINATION

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### S u m m a r y

Based on the experimental data, the article demonstrates the increase of the interatomic distances in a monocrystalline Si under the stationary illumination with white light. The appropriate estimation has been carried out in the harmonic approximation within the athermal mechanism of widening of semiconductors. The theoretical results are in good agreement with the experimental data.